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at least one Y-direction signal line crossing said X-direction signal line;

a thin film transistor formed over said substrate at an intersection of said X-direction signal line and said Y-direction signal line, said thin film transistor comprising an active layer comprising crystalline silicon including source, drain and channel regions;

a transparent electrode electrically connected to said thin film transistor;

an organic luminescence layer adjacent to said transparent electrode;

and

a peripheral driving circuit comprising another thin film transistor formed over said substrate for supplying a signal to one of said X-direction signal line and said Y-direction signal line.

Q1
Con'd.

11. (Amended) The display device according to claim 10 wherein said thin film transistor and said another thin film transistor are manufactured through the same process.

Q2

Please add new claims 15-18 as follows:

--15. An organic electroluminescence display device comprising:

a substrate having an insulating surface;

at least one X-direction signal line over said substrate;

at least one Y-direction signal line crossing said X-direction signal

line;

at least one pixel defined at an intersection between the X-direction signal line and the Y-direction signal line;

at least one switching thin film transistor and one current control thin film transistor provided over the substrate in said pixel;

Q3
Sub
Q2

an organic luminescence layer over the substrate; and
a peripheral driving circuit comprising at least a third thin film transistor formed over said substrate for supplying a signal to at least one of said X-direction signal line and said Y-direction signal line,

wherein each of the switching thin film transistor, the current control thin film transistor and the third thin film transistor comprises a semiconductor layer comprising crystalline silicon and including source, drain and channel regions, a gate insulating film adjacent to the semiconductor layer and a gate electrode adjacent the gate insulating film.

16. The display device according to claim 15 wherein said gate electrode is located over the channel region with the gate insulating film interposed therebetween.

103
cont.

17. An organic electroluminescence display device comprising:
a substrate having an insulating surface;
at least one X-direction signal line over said substrate;
at least one Y-direction signal line crossing said X-direction signal line;

Sub-
E3

at least one pixel defined at an intersection between the X-direction signal line and the Y-direction signal line;

at least one switching thin film transistor and one current control thin film transistor provided over the substrate in said pixel;

an organic luminescence layer over the substrate; and

a peripheral driving circuit comprising at least a third thin film transistor formed over said substrate for supplying a signal to at least one of said X-direction signal line and said Y-direction signal line,

wherein each of the switching thin film transistor, the current control thin film transistor and the third thin film transistor comprises a semiconductor layer

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comprising crystalline silicon and including source, drain and channel regions, a gate insulating film adjacent to the semiconductor layer and a gate electrode adjacent the gate insulating film, and is manufactured through the same process.

18. The display device according to claim 15 wherein said gate electrode is located over the channel region with the gate insulating film interposed therebetween.--
